

FIG. 1A

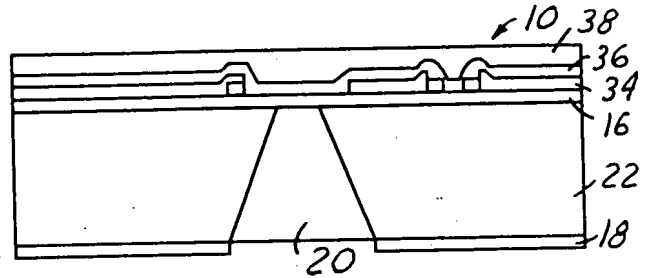


FIG. 1F

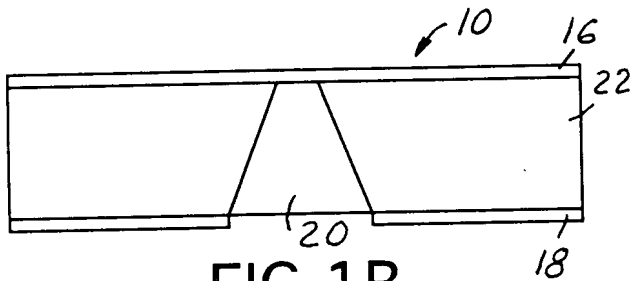


FIG. 1B

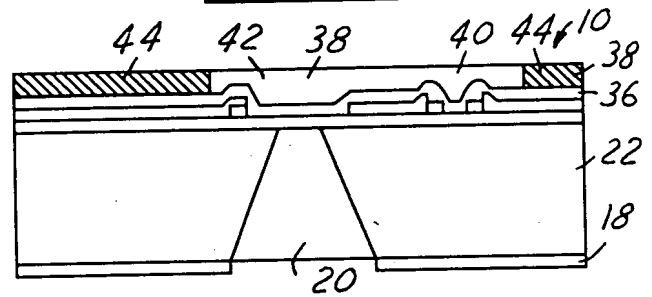


FIG. 1G

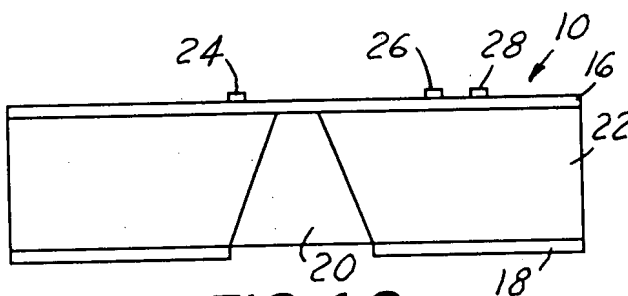


FIG. 1C

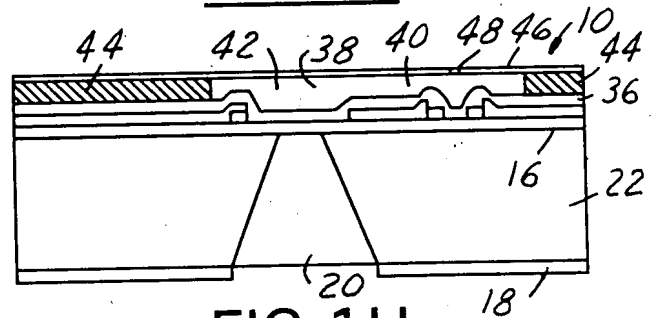


FIG. 1H

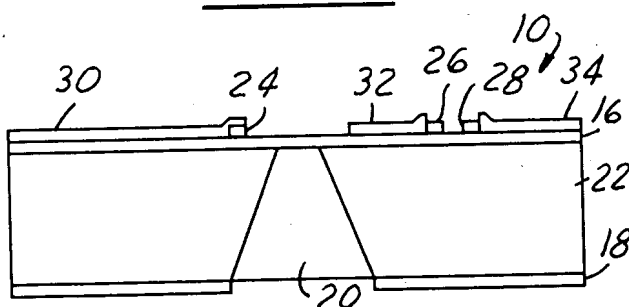


FIG. 1D

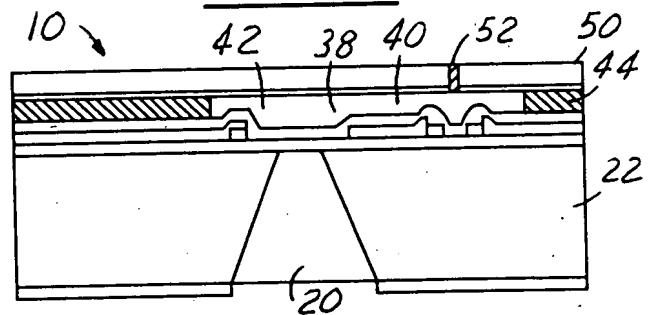


FIG. 1I

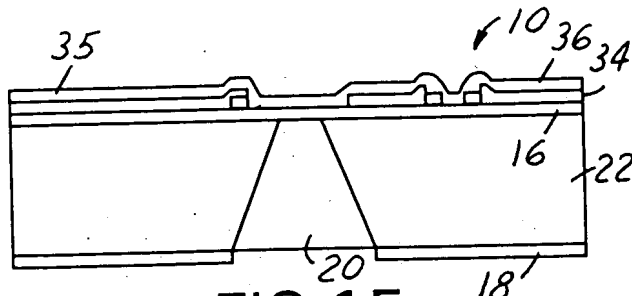


FIG. 1E

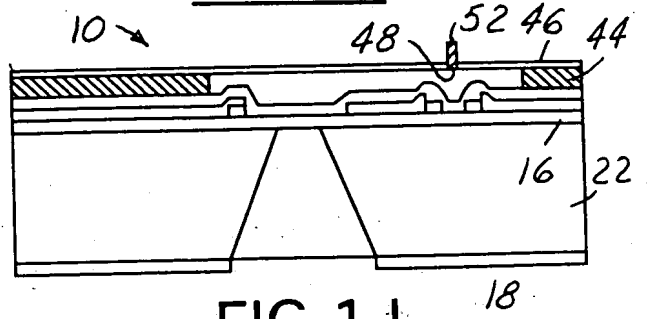


FIG. 1J

A cross-sectional view of a semiconductor device. The device features a tapered substrate, labeled 20, which is wider at the top and tapers downwards. The top surface of the substrate is covered by a multi-layered structure. From bottom to top, the layers are: a base layer 22, a layer 44 containing several small rectangular features, a layer 38, and a top layer 54. A vertical structure 52 is located on the right side of the top layer 54. A hatched rectangular region is shown on the left side of the device. A dimension line labeled 10 indicates the thickness of the top layer 54.

A cross-sectional view of a multi-layered structure. The structure consists of several layers. At the top, there is a thin layer labeled 42. Below it is a layer labeled 38. Under layer 38 is a layer labeled 50. Below layer 50 is a layer labeled 40. At the very top right, there is a small feature labeled 10. To the right of feature 10, there is a hatched area labeled 54. Below layer 40 is a layer labeled 44. At the bottom, there is a layer labeled 20. A trapezoidal feature labeled 16 is shown within the layer labeled 44. The entire structure is shown in a cross-sectional view.

A cross-sectional view of a semiconductor device, labeled 20, showing a central gap. The device consists of a substrate with a top layer 40. On the left side, there is a structure 62 with a top layer 56 and a side layer 58. On the right side, there is a structure 52 with a top layer 48. A central gap 60 is formed between the two structures.

FIG. 2

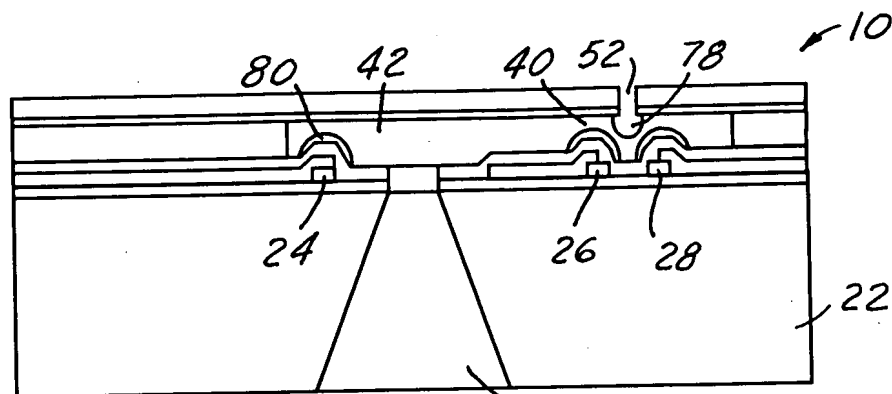


FIG. 3D

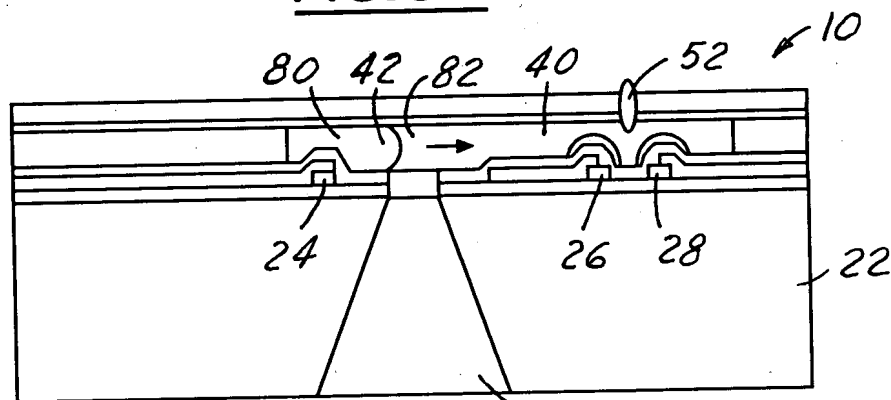


FIG. 3E

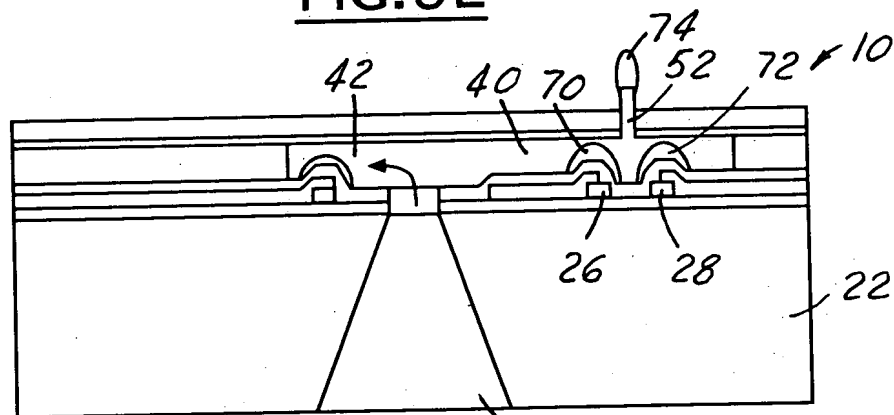


FIG. 3F

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